

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Currently Amended) An MIS-type field-effect transistor ~~characterized in~~ comprising:

- a base layer;
  - a strained active semiconductor layer formed on said base layer;
  - a gate insulating film formed on said active semiconductor layer;
  - a gate electrode formed on said gate insulating film; and
  - a source/drain region formed in portions on both sides of said gate electrode inside said active semiconductor layer; wherein
- an interface between said base layer and said active semiconductor layer is at a depth of  $2T_p$  or less from the surface, where  $T_p$  is the depth of maximum concentration of an impurity introduced for forming said source/drain region.

2. (Currently Amended) An MIS-type field-effect transistor ~~characterized in~~ comprising:

- a base layer;
  - a strained active semiconductor layer formed on said base layer;
  - a gate insulating film formed on said active semiconductor layer;
  - a gate electrode formed on said gate insulating film;
  - a source/drain region formed in portions on both sides of said gate electrode inside said active semiconductor layer; and
  - a gate side wall formed on the lateral face of said gate electrode; wherein
- a portion of said active semiconductor layer under said gate side wall and said gate electrode of said active semiconductor layer has a greater film thickness than any other portion of said active semiconductor layer; and
- an interface between said base layer and said active semiconductor layer is at a depth of  $2T_p$  or less from the surface of a region disposed other than under said gate side wall and

said gate electrode of said active semiconductor layer, where  $T_p$  is the depth of maximum concentration of an impurity introduced for forming said source/drain region.

3. (Currently Amended) An MIS-type field-effect transistor ~~characterized in~~ comprising:

- a base layer;
- a strained active semiconductor layer formed on said base layer;
- a gate insulating film formed on said active semiconductor layer;
- a gate electrode formed on said gate insulating layer; and
- a built-up layer provided with a source/drain region and formed on said active semiconductor layer on both sides of said gate electrode; wherein

said built-up layer has a film thickness of  $3T_p$  or greater, where  $T_p$  is the depth of maximum concentration of an impurity introduced for forming said source/drain region.

4. (Currently Amended) The MIS-type field-effect transistor according to claim 3, ~~characterized in that~~ wherein the film thickness of said built-up layer is  $5T_p$ .

5. (Currently Amended) The MIS-type field-effect transistor according to claim 1, ~~characterized in that~~ wherein said base layer is a semiconductor layer having the composition  $\text{Si}_{1-x-y}\text{Ge}_x\text{C}_y$  (wherein  $0 \leq x \leq 1$ ,  $0 \leq y \leq 1$ , and  $0 < x + y \leq 1$ ).

6. (Currently Amended) The MIS-type field-effect transistor according to claim 1, ~~characterized in that~~ wherein said base layer is an Si layer.

7. (Currently Amended) The MIS-type field-effect transistor according to claim 1, ~~characterized in that~~ wherein said base layer is a semiconductor layer, and an insulator layer is formed underneath said base layer.

8. (Currently Amended) The MIS-type field-effect transistor according to claim 1, ~~characterized in that~~ wherein said base layer is an insulator layer.

9. (Currently Amended) The MIS-type field-effect transistor according to claim 1, ~~characterized in that~~ wherein said active semiconductor layer is a group IV semiconductor layer.

10. (Currently Amended) The MIS-type field-effect transistor according to claim 1, ~~characterized in that~~ wherein said active semiconductor layer is an Si layer.

11. (Currently Amended) The MIS-type field-effect transistor according to claim 1, ~~characterized in that~~ wherein said active semiconductor layer is a semiconductor layer having the composition  $\text{Si}_{1-x-y}\text{Ge}_x\text{C}_y$  (wherein  $0 \leq x \leq 1$ ,  $0 \leq y \leq 1$ , and  $0 < x + y \leq 1$ ).

12. (Currently Amended) The MIS-type field-effect transistor according to claim 11, ~~characterized in~~ further comprising an Si layer with a film thickness of 10 nm or less between said active semiconductor layer and said gate insulating film.

13. (Currently Amended) The MIS-type field-effect transistor according to claim 1, ~~characterized having~~ wherein the MIS-type field effect transistor has a gate length of 0.4  $\mu\text{m}$  or less.

14. (Currently Amended) The MIS-type field-effect transistor according to claim 1, ~~characterized in that~~ wherein said source/drain region is formed by an ion implantation method.

15. (Currently Amended) The MIS-type field-effect transistor according to claim 1, ~~characterized in that~~ wherein said source/drain region is formed by a plasma doping method.

16. (Currently Amended) The MIS-type field-effect transistor according to claim 1, ~~characterized in that~~ wherein said source/drain region is formed by a gas-phase doping method.

17. (Currently Amended) The MIS-type field-effect transistor according to ~~any~~ claim 1, ~~characterized in that~~ wherein a portion of said source/drain region near the gate electrode is a region of low impurity concentration.